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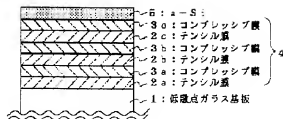
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APPLICANT : SANYO ELECTRIC CO LTD;

INVENTOR : HARADA YASUKI;

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TITLE : AMORPHOUS-SEMICONDUCTOR
FORMATION SUBSTRATE AND
MANUFACTURE OF
POLYCRYSTALLINE-SEMICONDUCTOR
FORMATION SUBSTRATE USING IT



ABSTRACT : PURPOSE: To provide an amorphous semiconductor formation substrate whose film thickness is comparatively thick so as not to thermally damage a low-melting-point glass substrate and which is provided with a buffer layer not increasing an internal stress due to the thick film thickness.

CONSTITUTION: An amorphous semiconductor formation substrate is formed in such a way that an a-Si film 5 is formed on a low-melting-point glass substrate 1 via a buffer layer 4 for impurity-diffusion prevention. In the formation substrate, the buffer layer 4 is formed of a film in which tensile films 2a to 2c composed of SiO₂ and compressive films 3a to 3c composed of SiO₂ in the same manner have been laminated alternately.

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